

2.5V Drive Nch+SBD MOSFET

ES6U41

●Structure

Silicon N-channel MOSFET /
Schottky barrier diode

●Features

- 1) Nch MOSFET and schottky barrier diode-
are put in WEMT6 package.
- 2) High-speed switching, Low On-resistance.
- 3) Low voltage drive (2.5V drive).
- 4) Built-in Low V_F schottky barrier diode.

●Applications

Switching

●Package specifications

Type	Package	Taping
	Code	T2R
	Basic ordering unit (pieces)	8000
ES6U41		○

●Absolute maximum ratings (Ta=25°C)

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Parameter	Symbol	Limits	Unit	
Drain-source voltage	V_{DSS}	30	V	
Gate-source voltage	V_{GSS}	±12	V	
Drain current	Continuous	I_D	±1.5	A
	Pulsed	I_{DP} *1	±6.0	A
Source current (Body diode)	Continuous	I_S	0.75	A
	Pulsed	I_{SP} *1	6.0	A
Channel temperature	T_{ch}	150	°C	
Power dissipation	P_D *2	0.7	W / ELEMENT	

*1 $P_w \leq 10\mu s$, Duty cycle ≤ 1%
*2 Mounted on a ceramic board

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Parameter	Symbol	Limits	Unit
Repetitive peak reverse voltage	V_{RM}	25	V
Reverse voltage	V_R	20	V
Forward current	I_F	0.5	A
Forward current surge peak	I_{FSM} *1	2.0	A
Junction temperature	T_j	150	°C
Power dissipation	P_D *2	0.5	W / ELEMENT

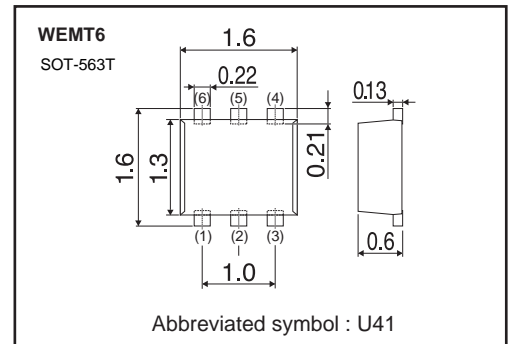
*1 60Hz · 1 cycle
*2 Mounted on ceramic board

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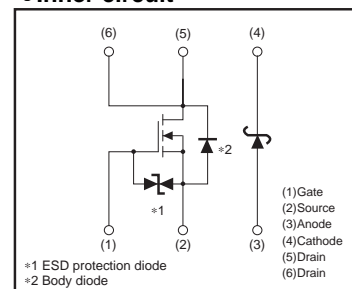
Parameter	Symbol	Limits	Unit
Power dissipation	P_D *	0.8	W / TOTAL
Range of storage temperature	T_{stg}	-55 to +150	°C

* Mounted on a ceramic board

●Dimensions (Unit : mm)



●Inner circuit



●Electrical characteristics

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Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS}=\pm 12V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.5	-	1.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	-	170	240	m Ω	$I_D=1.5A, V_{GS}=4.5V$
		-	180	250	m Ω	$I_D=1.5A, V_{GS}=4V$
		-	240	340	m Ω	$I_D=1.5A, V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $ *	1.5	-	-	S	$V_{DS}=10V, I_D=1.5A$
Input capacitance	C_{iss}	-	80	-	pF	$V_{DS}=10V$
Output capacitance	C_{oss}	-	14	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	-	12	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	-	7	-	ns	$V_{DD}\doteq 15V$
Rise time	t_r *	-	9	-	ns	$I_D=0.75A$
Turn-off delay time	$t_{d(off)}$ *	-	15	-	ns	$V_{GS}=4.5V$
Fall time	t_f *	-	6	-	ns	$R_L\doteq 20\Omega$
Total gate charge	Q_g *	-	1.6	2.2	nC	$V_{DD}\doteq 15V, V_{GS}=4.5V$
Gate-source charge	Q_{gs} *	-	0.5	-	nC	$I_D=1.5A, R_L\doteq 10\Omega$
Gate-drain charge	Q_{gd} *	-	0.3	-	nC	$R_G=10\Omega$

*Pulsed

<Body diode characteristics (Source-drain)>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	-	-	1.2	V	$I_S=0.75A, V_{GS}=0V$

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Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.36	V	$I_F=0.1A$
		-	-	0.52	V	$I_F=0.5A$
Reverse current	I_R	-	-	100	μA	$V_R=20V$

●Electrical characteristics curves
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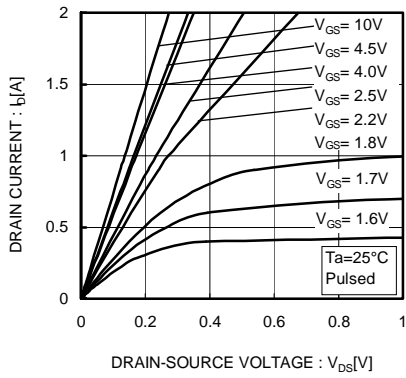


Fig.1 Typical Output Characteristics (I)

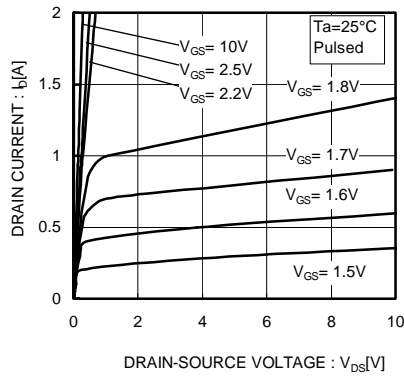


Fig.2 Typical Output Characteristics (II)

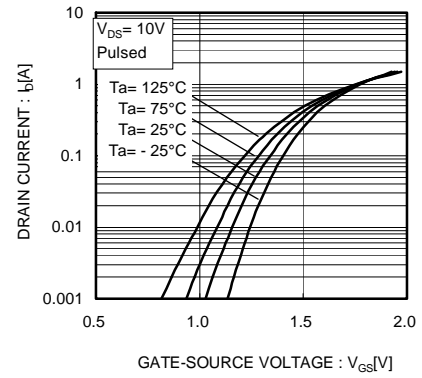


Fig.3 Typical Transfer Characteristics

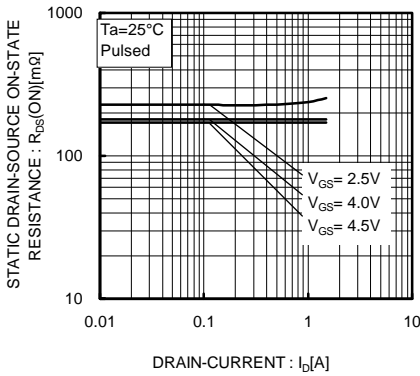


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (I)

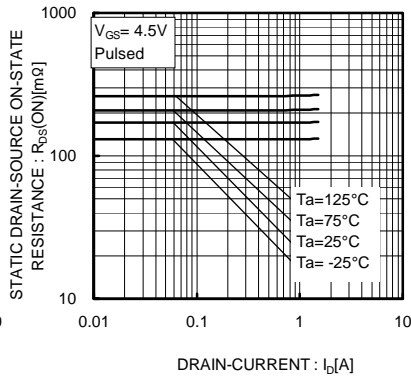


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (II)

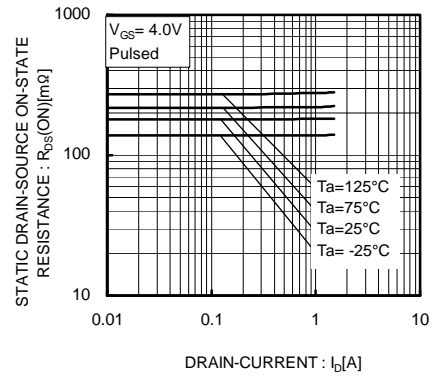


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current (III)

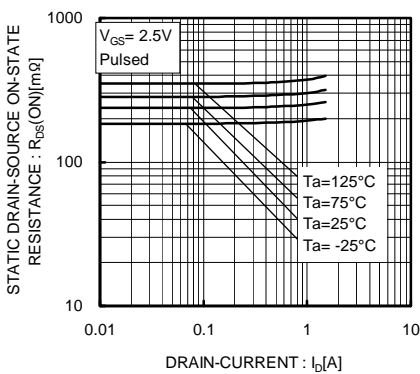


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (IV)

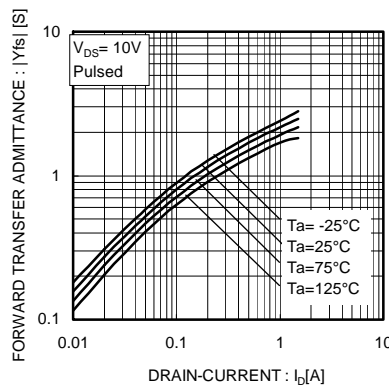


Fig.8 Forward Transfer Admittance vs. Drain Current

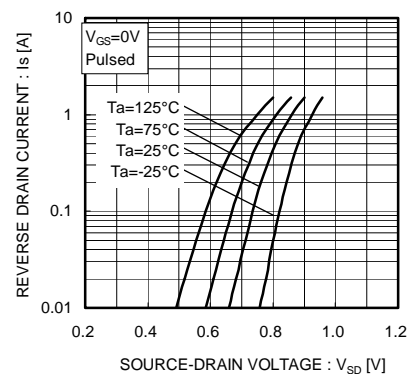


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

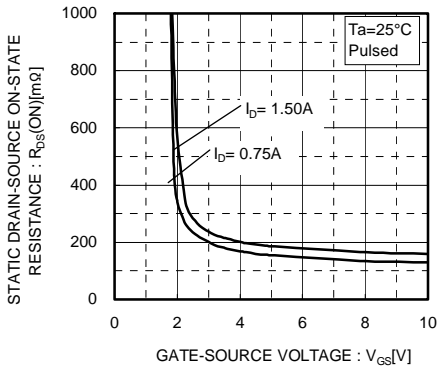


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

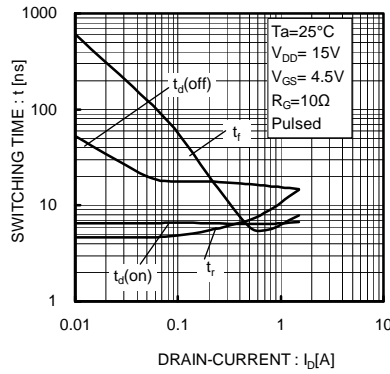


Fig.11 Switching Characteristics

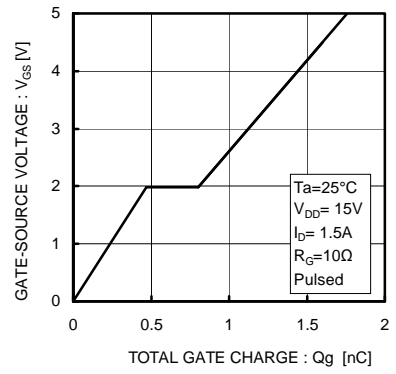


Fig.12 Dynamic Input Characteristics

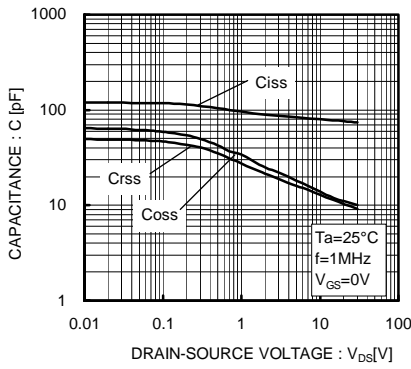


Fig.13 Typical Capacitance vs. Drain-Source Voltage

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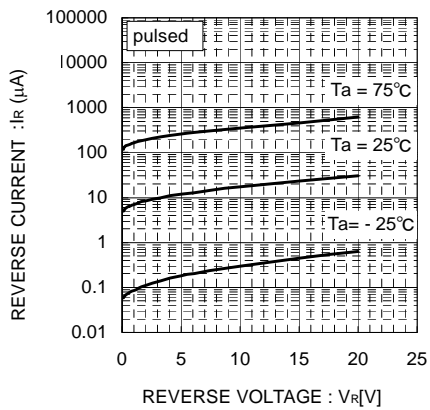


Fig.1 Reverse Current vs. Reverse Voltage

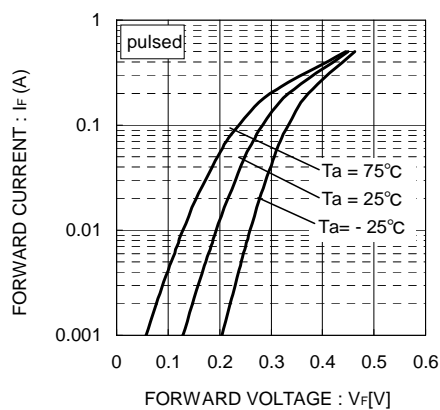


Fig.2 Forward Current vs. Forward Voltage

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